Photocoupler

K401 • K402 • K404

These Photocouplers consist of two Gallium Arsenide Infrared Emitting Diodes and a Silicon NPN Photo Darlington transistor per a channel.

The K401 has one channel in a 4-pin mini-flat SMD package.
The K402 has two channels in a 8-pin mini-flat SMD package.
The K404 has four channels in a 16-pin mini-flat SMD package.

FEATURES

- Mini-flat Package
- Collector-Emitter Voltage : Min.30V
- Current Transfer Ratio : Type 600%
  (at I_F=±1mA, V_{CE}=2V)
- Electrical Isolation Voltage : AC3750V_{rms}

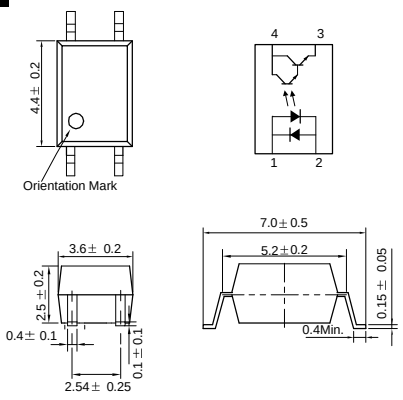
APPLICATIONS

- AC Signal Input
- Interface between two circuits of different potential
- Automatic Vending Machine
- Copiers, Industrial Robots

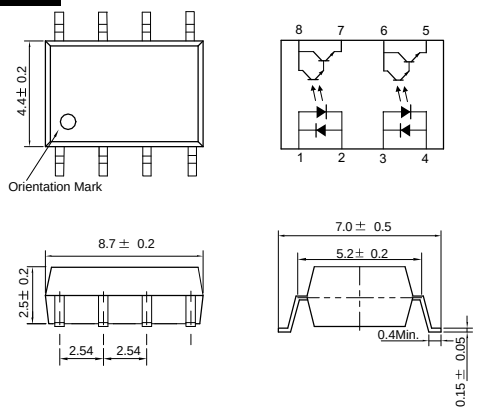
DIMENSION

(Unit : mm)

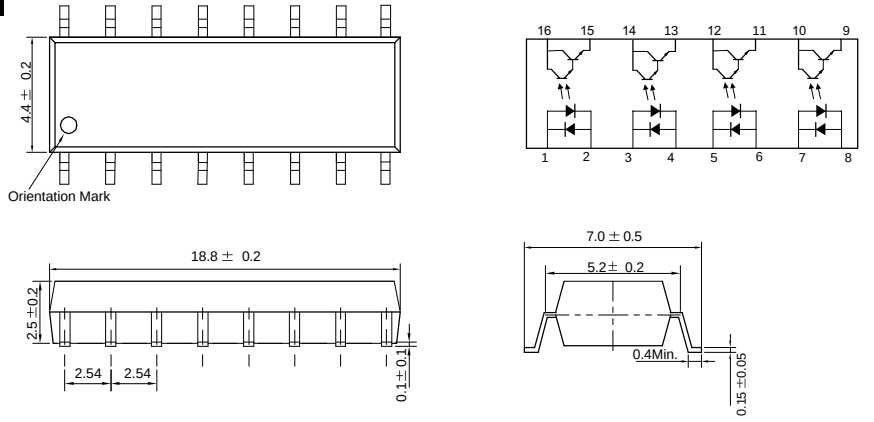
K401



K402



K404



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MAXIMUM RATINGS (Ta=25℃)

Parameter		Symbol	Rating	Unit
Input	Forward Current	I_F	±50	mA
	Peak Forward Current[*1]	I_{FP}	±1	A
	Power Dissipation	P_D	70	mW
	Junction temperature	T_J	125	℃
Output	Collector-Emitter Breakdown Voltage	BV_{CEO}	30	V
	Emitter-Collector Breakdown Voltage	BV_{ECO}	5	V
	Collector Current	I_C	50	mA
	Collector Power Dissipation	P_C	150	mW
Input to Output Isolation Voltage[*2]		V_{iso}	AC3750	V_{rms}
Storage Temperature		T_{stg}	-55~+125	℃
Operating Temperature		T_{opr}	-30~+85	℃
Lead Soldering Temperature[*3]		T_{sol}	260	℃
Total Power Dissipation		P_{tot}	250	mW

*1. Input current with 100μs pulse width, 1% duty cycle

*2. Measured at RH=40~60% for 1min

*3. 1/16 inch form case for 10sec

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25 , unless otherwise noted)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit.
Input	Forward Voltage	V_F	I_F= ±10mA	-	1.15	1.30	V
	Capacitance	C_T	V=0, f=1kHz	-	30	-	pF
Output	Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=0.5mA	30	-	-	V
	Emitter-Collector Breakdown Voltage	BV_{ECO}	I_E=0.1mA	5	-	-	V
	Collector Dark Current	I_{CEO}	I_F=0, V_{CE}=10V	-	-	100	nA
	Capacitance	C_{CE}	V_{CE}=0, f=1KHz	-	10	-	pF
Coupled	Current Transfer Ratio[*4]	CTR	I_F= ±1mA, V_{CE}=2V	300	-	-	%
	Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_F= ±1mA, I_C=2mA	-	0.8	1.2	V
	Input-Output Capacitance	C_{IO}	V=0, f=1KHz	-	5	-	pF
	Input-Output Isolation Resistance	R_{IO}	RH=40~60%, V=500V	-	10^{11}	-	Ω
	Rise Time	tr	V_{CE}=10V, R_L=100	-	90	-	μs
	Fall Time	tf	I_C=10mA	-	120	-	μs

*4. CTR=(I_C/I_F) X 100 (%)

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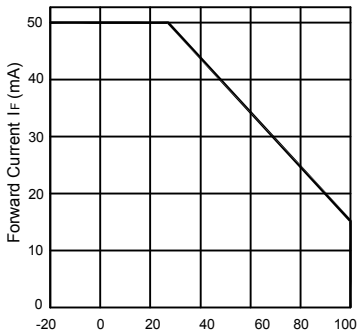
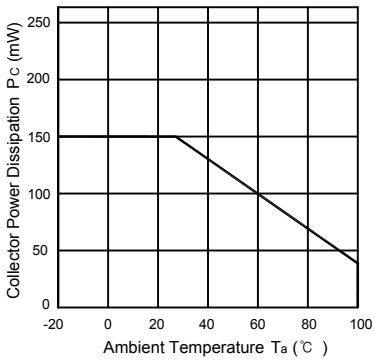
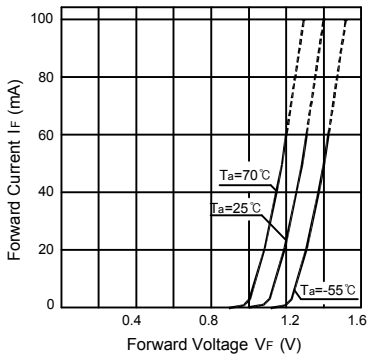
Forward Current vs. Ambient Temperature



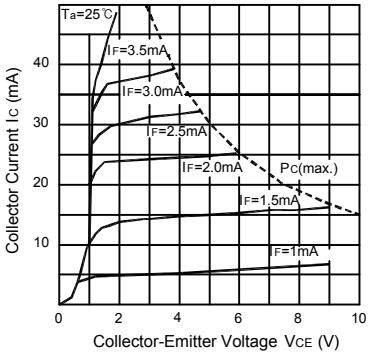
Collector Power Dissipation vs. Ambient Temperature



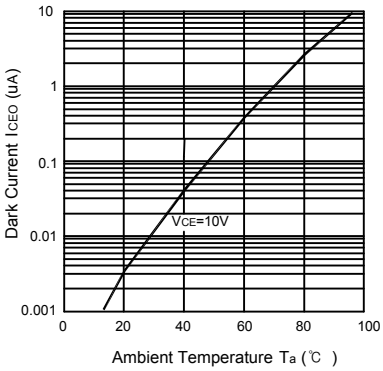
Forward Current vs. Forward Voltage



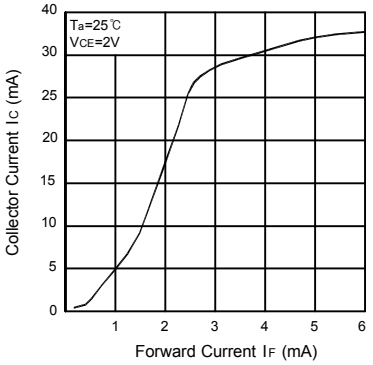
Collector Current vs. Collector-Emitter Voltage



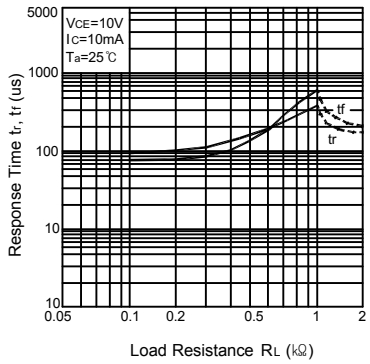
Dark Current vs. Ambient Temperature



Collector Current vs. Forward Current



Response Time vs. Load Resistance



Switching Time Test Circuit